Micro Commercial Components
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BUH517

NPN Silicon Power Transistors

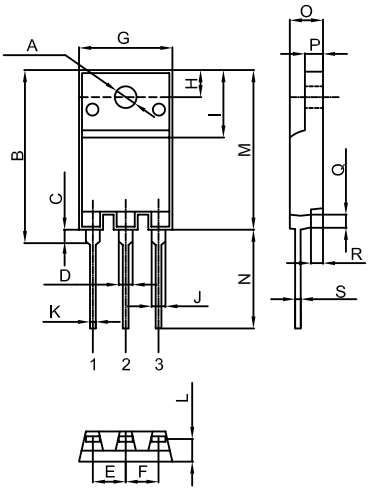
Features

- High voltage, fast switching NPN power transistors.
- With TO-3PML package
- Manufactured using multiepitaxial mesa technology for cost-effective high performance abd use a hollow emitter structure to enhance switching speeds.

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	700	V
V_{CBO}	Collector-Base Voltage	1700	V
V_{EBO}	Emitter-Base Voltage	10	V
I_{CP}	Peak Collector Current	12	A
I_C	Collector Current	8.0	A
P_C	Collector power dissipation	60	W
T_J	Junction Temperature	-55 to +150	^{O}C
T_{STG}	Storage Temperature	-55 to +150	^{O}C

TO-3PML



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	.13	.14	3.20	3.60	Ø
B	.81	.84	20.70	21.30	
C	.15	.17	3.80	4.20	
D	.10	.12	2.50	3.10	
E	.21	.22	5.25	5.65	
F	.21	.22	5.25	5.65	
G	.62	.64	15.80	16.20	
H	.19	.21	4.70	5.30	
I	.30	.33	7.70	8.30	
J	.07	.09	1.70	2.30	
K	.03	.05	.70	1.30	
L	.13	.15	3.20	3.80	
M	.85	.88	21.70	22.30	
N	.78	.82	19.90	20.90	
O	.21	.23	5.30	5.90	
P	.11	.13	2.80	3.40	
Q	.07	.09	1.70	2.30	
R	.07	.09	1.70	2.30	
S	.02	.03	.40	.80	

Electrical Characteristics @ 25^{O}C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (I_C=100mAdc, I_B=0)	700	---	Vdc
I_{CBO}	Collector-Base Cutoff Current (V_{CB}=1500Vdc,I_E=0)	---	0.2	mAdc
I_{EBO}	Emitter-Base Cutoff Current (V_{EB}=5.0Vdc, I_C=0)	---	100	uAdc
ON CHARACTERISTICS				
h_{FE}	Forward Current Transfer ratio (I_C=5.0Adc, V_{CE}=5.0Vdc)	6.0	12	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage (I_C=5.0Adc, I_B=1.25Adc)	---	1.5	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage (I_C=5.0Adc,I_B=1.25Adc)	---	1.3	Vdc